

### FEATURES

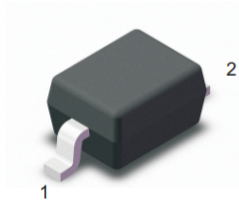
- For surface mounted applications
- Glass Passivated Chip Junction
- Fast reverse recovery time
- Ideal for automated placement
- Lead free in comply with EU RoHS 2011/65/EU directives

### MECHANICAL DATA

- Case: SOD-323
- Terminals: Solderable per MIL-STD-750, Method 2026

### PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Top View  
Simplified outline SOD-323 and symbol



### Absolute Maximum Ratings at 25 °C

Parameter	Symbols	BAS21VM	Units
Maximum Repetitive Peak Reverse Voltage	$V_{RRM}$	250	V
Maximum RMS voltage	$V_{RMS}$	200	V
Continuous Forward Current	$I_F$	250	mA
Repetitive Peak Forward Current	$I_{FRM}$	625	mA
Non-reptitive Peak Forward Surge Current	$I_{FSM}$	1 3 9	A
		at 1s	
		at 1ms	
		at 1 us	
Total Power Dissipation	$P_{tot}$	500	mW
Operating and Storage Temperature Range	$T_j, T_{stg}$	-55 ~ +150	°C

Characteristics at  $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbols	BAS21VM	Units
Reverse Breakdown Voltage at $I_R=100\mu\text{A}$	$V_{(BR)R}$	250	V
Maximum Forward Voltage at 100 mA at 200 mA	$V_F$	1.00 1.25	V
Maximum DC Reverse Current at Rated DC Blocking Voltage $T_a = 25\text{ }^\circ\text{C}$ $T_a = 150\text{ }^\circ\text{C}$	$I_R$	0.1 100	$\mu\text{A}$
Typical Junction Capacitance at $V_R=4\text{V}$ , $f=1\text{MHz}$	$C_j$	5	pF
Maximum Reverse Recovery Time	$t_{rr}$	50	ns

Fig.1 Forward Current Derating Curve

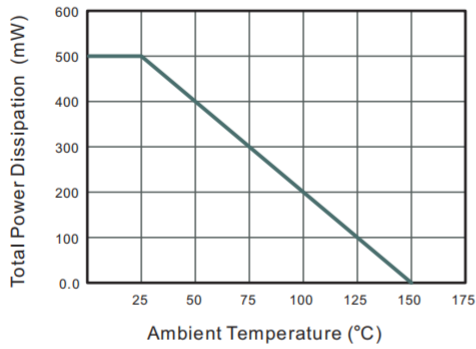


Fig.2 Typical Reverse Characteristics

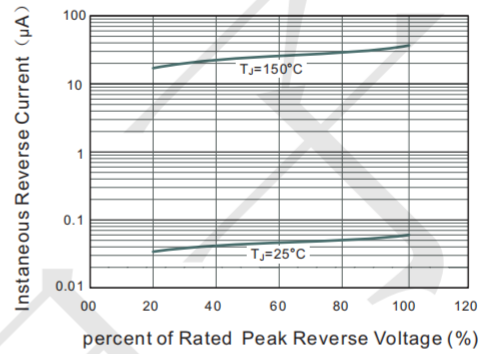


Fig.3 Typical Instantaneous Forward Characteristics

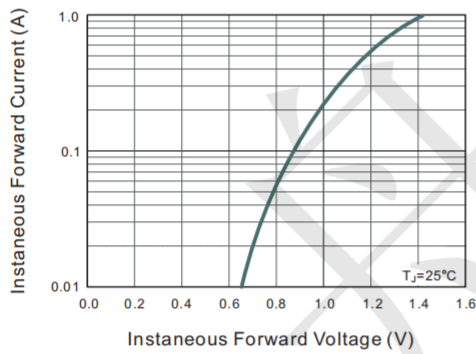
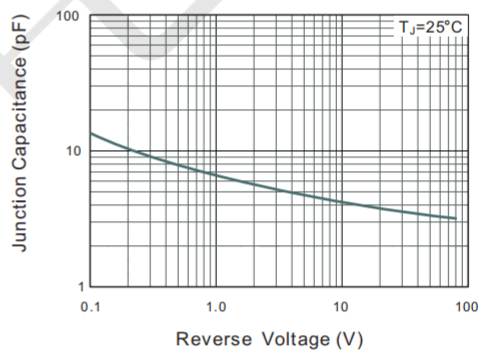
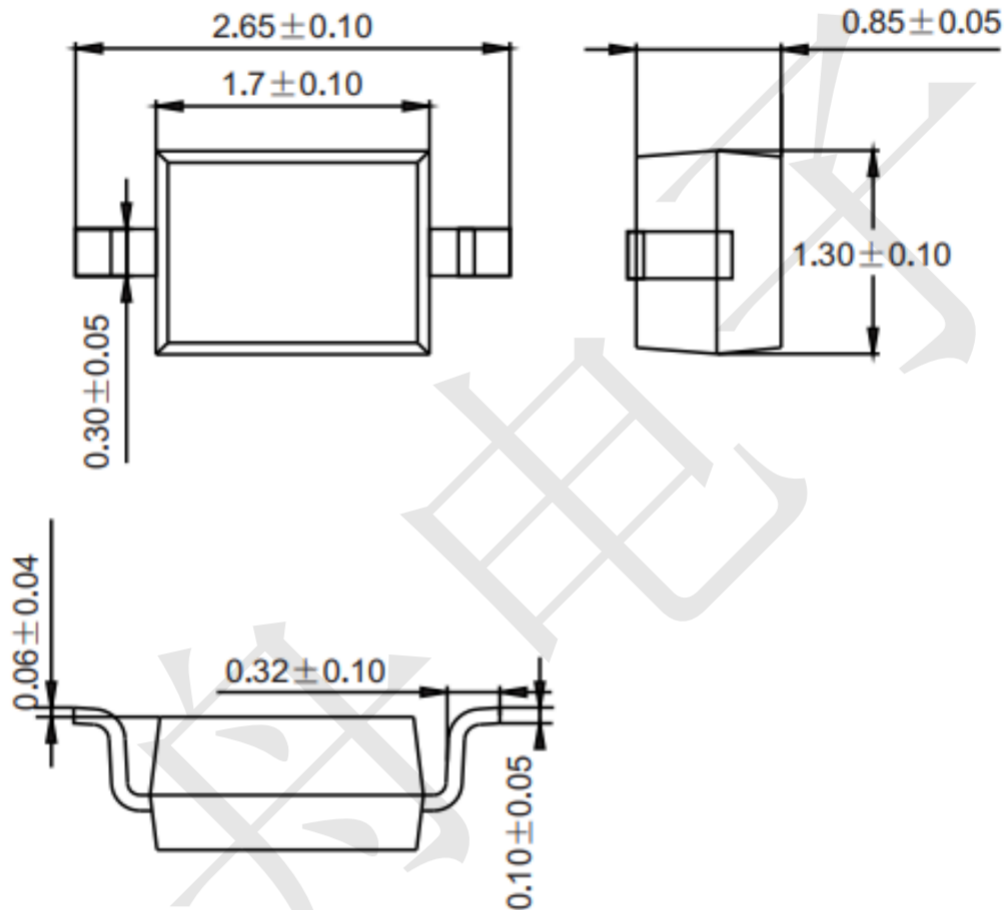


Fig.4 Typical Junction Capacitance



### Package information (Unit: mm)

#### SOD-323



### Mounting Pad Layout (Unit: mm)

